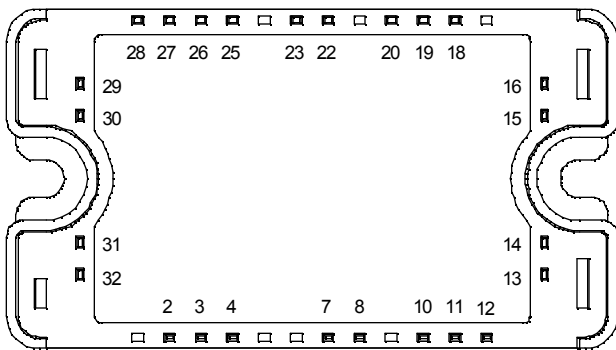
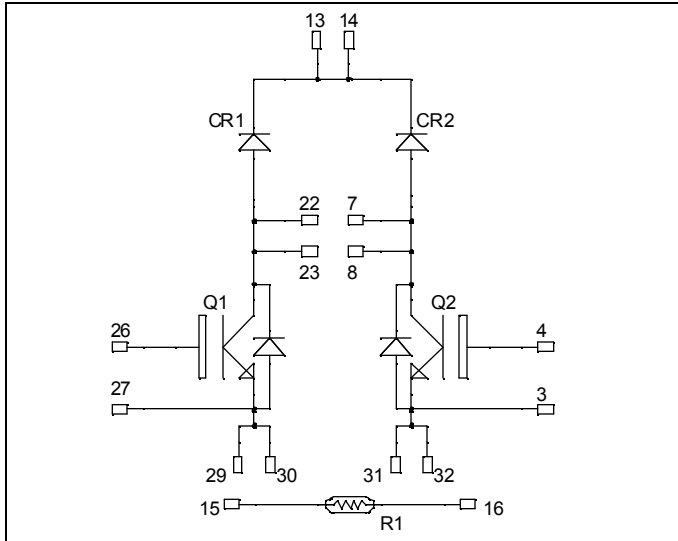


Dual Boost chopper
Trench IGBT® Power Module

V_{CES} = 1200V
I_C = 50A @ T_c = 80°C



All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of V_{CEsat}
- Each leg can be easily paralleled to achieve a single boost of twice the current capability.

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage	1200	V
I _C	Continuous Collector Current	T _C = 25°C	75
		T _C = 80°C	50
I _{CM}	Pulsed Collector Current	T _C = 25°C	100
V _{GE}	Gate - Emitter Voltage	±20	V
P _D	Maximum Power Dissipation	T _C = 25°C	270
RBSOA	Reverse Bias Safe Operating Area	T _J = 125°C	100A @ 1150V

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 2mA$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			5	mA
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 50A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.4 2.0	2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$	5.0	5.8	6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		3600		pF
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		160		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$ $R_G = 18\Omega$		90		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			420		
T_f	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$ $R_G = 18\Omega$		90		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			520		
T_f	Fall Time			90		
E_{on}	Turn-on Switching Energy ❶			5		mJ
E_{off}	Turn-off Switching Energy ❷			5.5		

❶ E_{on} includes diode reverse recovery

❷ In accordance with JEDEC standard JESD24-1

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		250 500	μA
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle		60		A
V_F	Diode Forward Voltage	$I_F = 60A$ $I_F = 120A$ $I_F = 60A$	$T_j = 125^\circ\text{C}$	2 2.3 1.8	2.5	V
t_{rr}	Reverse Recovery Time	$I_F = 60A$ $V_R = 800V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	400 470		ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1200 4000		nC

Temperature sensor NTC

Symbol Characteristic

		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		68		kΩ
B _{25/85}	T ₂₅ = 298.16 K		4080		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

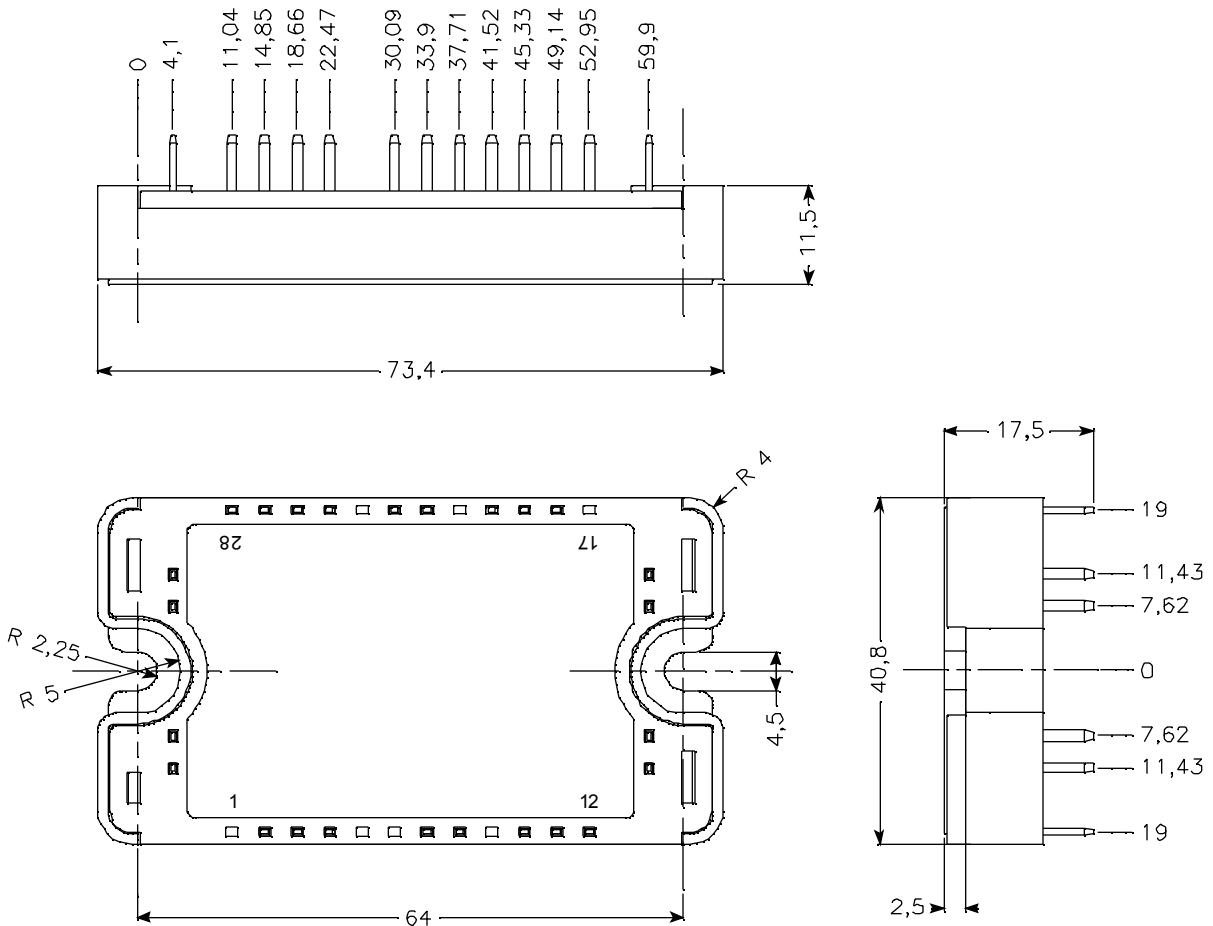
T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

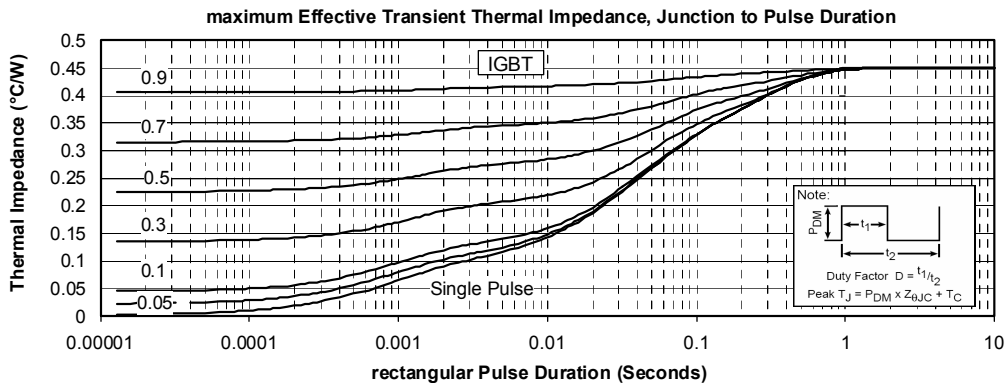
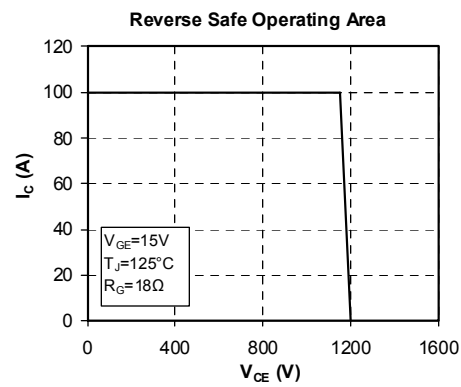
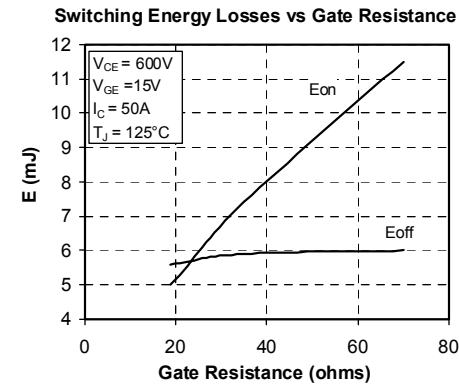
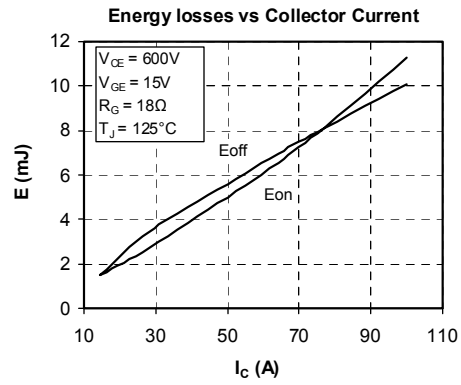
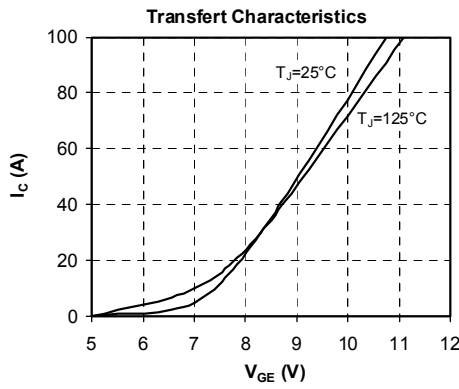
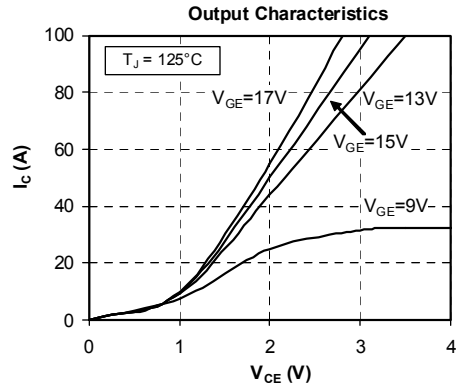
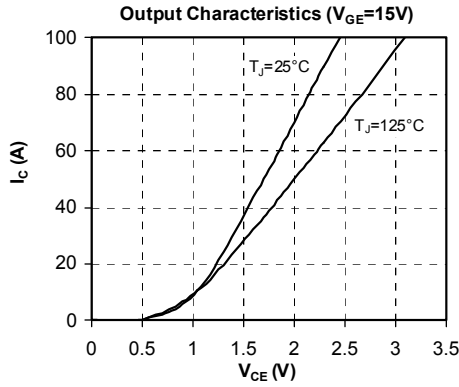
Symbol Characteristic

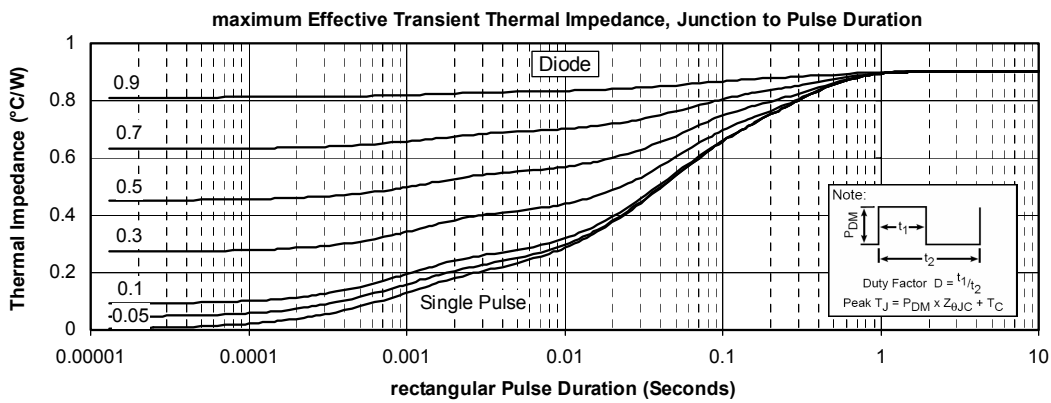
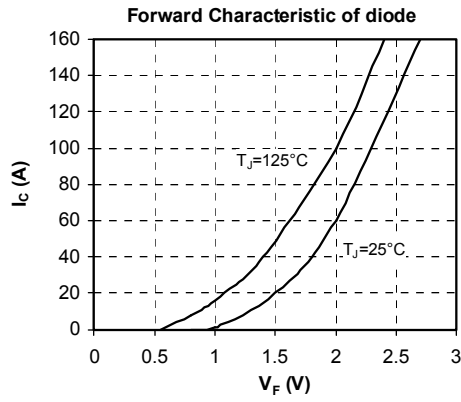
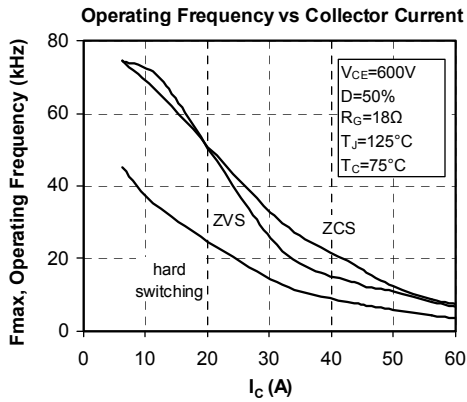
		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
R _{thJC}	Junction to Case	IGBT		0.45	°C/W	
		Diode		0.9		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque		To heatsink	M4	4.7	N.m
Wt	Package Weight				110	g

Package outline



Typical Performance Curve





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.